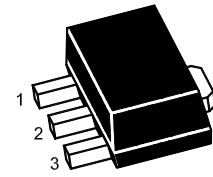


NPN Silicon Power Transistor

The transistor is subdivided into four groups, R, Q, P and E, according to its DC current gain.



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

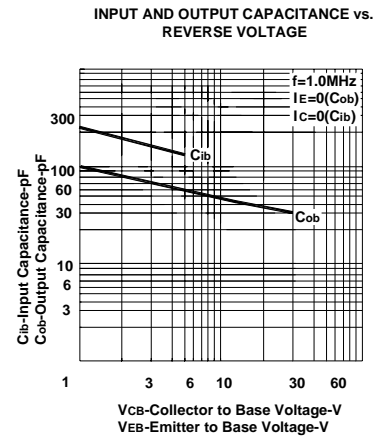
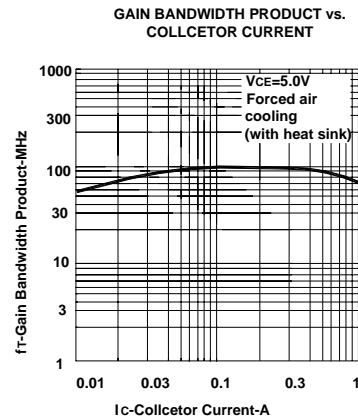
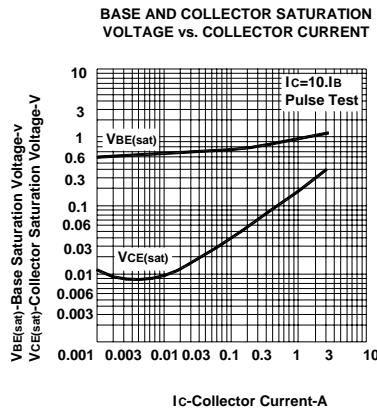
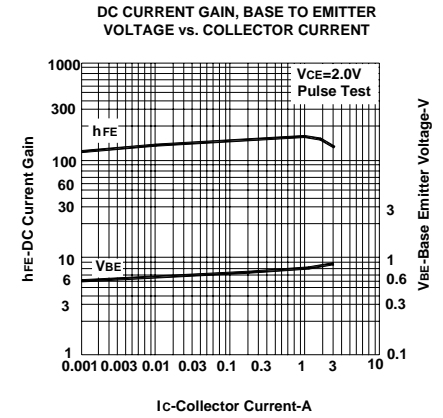
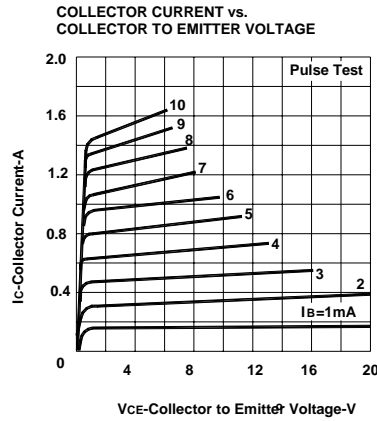
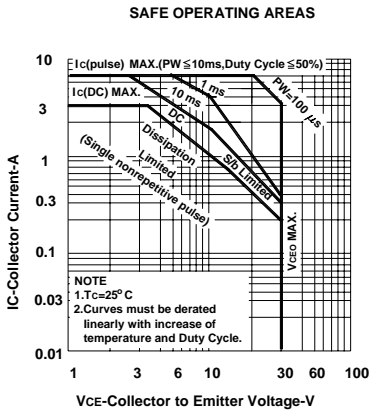
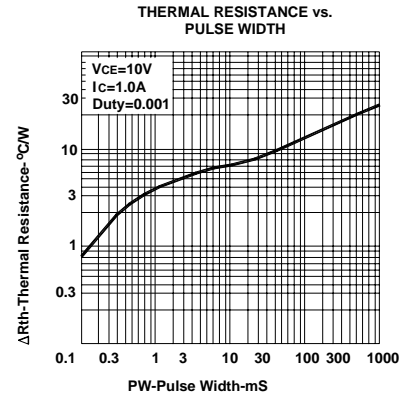
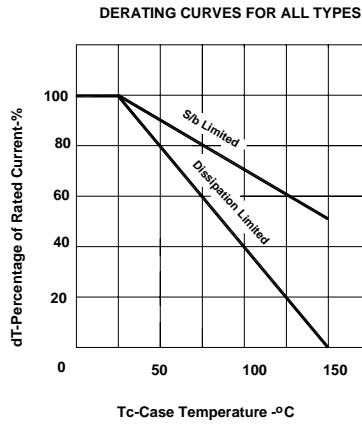
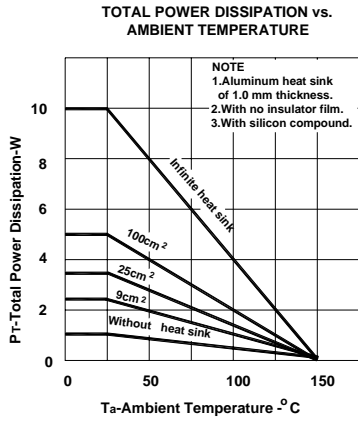
Absolute Maximum Ratings (T_a = 25 °C)

| Parameter | Symbol | Value | Unit |
|--|------------------|---------------|------|
| Collector to Base Voltage | V _{CB0} | 40 | V |
| Collector to Emitter Voltage | V _{CEO} | 30 | V |
| Emitter to Base Voltage | V _{EBO} | 5 | V |
| Collector Current | I _C | 3 | A |
| Peak Collector Current (t = 10 ms) | I _{CP} | 7 | A |
| Total power dissipation (T _a = 25 °C) | P _{tot} | 1 | W |
| Total power dissipation (T _c = 25 °C) | P _{tot} | 10 | W |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | T _{stg} | - 55 to + 150 | °C |

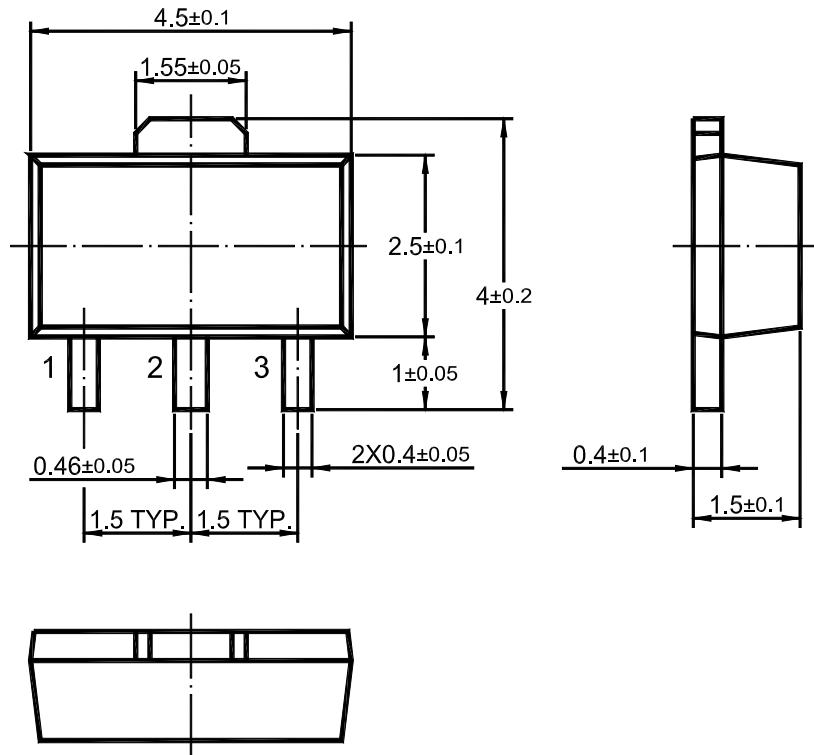
Characteristics at T_a = 25 °C

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|---|----------------------|------|------|------|------|
| DC Current Gain at V _{CE} = 2 V, I _C = 20 mA at V _{CE} = 2 V, I _C = 1 A Current Gain Group | R | 30 | - | - | - |
| | Q | 60 | - | 120 | - |
| | P | 100 | - | 200 | - |
| | E | 160 | - | 320 | - |
| | E | 200 | - | 400 | - |
| Collector Base Cutoff Current at V _{CB} = 30 V | I _{CB0} | - | - | 1 | µA |
| Emitter Base Cutoff Current at V _{EB} = 3 V | I _{EBO} | - | - | 1 | µA |
| Collector Emitter Saturation Voltage at I _C = 2 A, I _B = 0.2 A | V _{CE(sat)} | - | - | 0.5 | V |
| Base Emitter Saturation Voltage at I _C = 2 A, I _B = 0.2 A | V _{BE(sat)} | - | - | 2 | V |
| Gain Bandwidth Product at V _{CE} = 5 V, I _C = 0.1 A | f _T | - | 90 | - | MHz |
| Output Capacitance at V _{CB} = 10 V, f = 1 MHz | C _{ob} | - | 45 | - | pF |

TYPICAL CHARACTERISTICS (Ta=25°C)



SOT-89 PACKAGE OUTLINE



Dimensions in mm

单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)